

A detailed cross-sectional diagram of a semiconductor device. The structure consists of several stacked layers and regions. At the base is a substrate labeled 'A'. Above it are various layers and structures: a layer labeled 'B' containing regions '10' and '60'; a layer labeled '15' containing regions '15A' and '15B'; a layer labeled '20' containing regions '20A' and '20B'; and a top layer labeled '21' containing region '22'. On the right side, there is a complex structure labeled '1' which includes a layer '3' with a small protrusion '11B', a layer 'S1' with a notch '4A', a layer '4' with a notch '5V', and a layer '5' with a notch '5H'. This structure is adjacent to another layer labeled 'S2' and a large, rounded component labeled '50'. Various other labels like '17', '11', '15A', '4A', '6', '5V', and '5H' indicate specific features or interfaces between the layers.







